

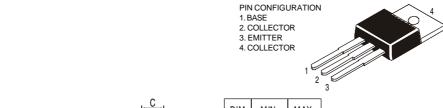


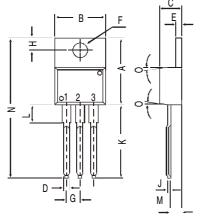


TO-220 Plastic Package

BD949, BD951, BD953, BD955 BD950, BD952, BD954, BD956

BD949, 951, 953, 955 NPN PLASTIC POWER TRANSISTORS BD950, 952, 954, 956 PNP PLASTIC POWER TRANSISTORS Power Amplifier and Switching Applications





diminsions in mm.	DIM	MIN.	MAX.		
	Α	14.42	16.51		
	В	9.63	10.67		
	С	3.56	4.83		
	D		0.90		
	Е	1.15	1.40		
	F	3.75	3.88		
	G	2.29	2.79		
	Н	2.54	3.43		
	J		0.56		
	K	12.70	14.73		
	L	2.80	4.07		
	М	2.03	2.92		
	N		31.24		
Ē	0	DEG 7			

ABSOLUTE MAXIMUM RATINGS

		949	951	953	955	
		950	952	954	956	
Collector-base voltage (open emitter)	V_{CBO}	max. 60	80	100	120	V
Collector-emitter voltage (open base)	V_{CEO}	max. 60	80	100	120	V
Collector current	I_C	max.	5.	.0		A
Total power dissipation up to $T_{mb} = 25^{\circ}C$	P_{tot}	max.	4	0		W
Junction temperature	T_{j}	max.	13	50		$^{\circ}C$
Collector-emitter saturation voltage	,					
$I_C = 2 A; I_B = 0.2 A$	V_{CEsat}	max.	1	.0		V
D.C. current gain						
$I_C = 2 A; V_{CE} = 4 V$	h_{FE}	min.	2	0		
PATTINGS (A TILL 250G)						

RATINGS (at T_A =25°C unless otherwise specified) Limiting values

Limiting values		949	951	953	955	
		950	952	954	956	
Collector-base voltage (open emitter)	V_{CBO}	max. 60	80	100	120	V
Collector-emitter voltage (open base)	V_{CEO}	max. 60	80	100	120	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	.0		V
Collector current	I_C	max.	5	.0		A

BD949, BD951, BD953, BD955 BD950, BD952, BD954, BD956

Collector current (Peak value) Fotal power dissipation upto T _{mb} =25°C unction temperature Storage temperature		I_{CM} P_{tot} T_j T_{stg}	max. max. max.	8.0 40 150 -65 to +150		150	$\begin{matrix} A \\ W \\ {}^{\circ}C \\ {}^{\circ}C \end{matrix}$
THERMAL RESISTANCE From junction to ambient From junction to mounting base		R _{th j–a} R _{th j–mb}		70 3.12			K/W K/W
CHARACTERISTICS $T_{amb} = 25^{\circ}\text{C}$ unless of	herwise specified		949 950	951 952	953 954	955 956	
Callactor outoff aurmant	4		930	932	934	930	
Collector cutoff current $I_E = 0$; $V_{CB} = V_{CBC}$		Iana	111 a x	5	0		11.Λ
$I_E = 0, V_{CB} = V_{CBC}$ $I_E = 0, V_{CB} = \frac{1}{2} V_{CB}$		I _{CBO} I _{CBO}	max.		.0		μA m A
$I_{B} = 0$, $V_{CB} = \frac{1}{2}$ V_{C}		ICEO	max. max.		.0 .1		mA
Emitter cut-off current	LEO	ICEO	mux.	U	. 1		111.21
$I_C = 0; V_{EB} = 5 V$		I_{EBO}	max.	0	.2		mA
Breakdown voltages		1EBO	mux.	U			111.21
$I_C = 1 \text{ mA}; I_B = 0$		V_{CEO}	min. 60	80	100	120	V
$I_C = 1 mA$; $I_E = 0$		V_{CBO}	min. 60	80	100	120	$\stackrel{\scriptstyle V}{V}$
$I_E = 1 \text{ mA}; I_C = 0$		V_{EBO}	min.		.0	120	$\stackrel{\scriptstyle V}{V}$
IE = I mA, IC = 0 Saturation voltage		v EBO	111111.	J	.0		V
$I_C = 2 A$; $I_B = 0.2 A$	Δ	V_{CEsat}^*	max.	1	0		V
Base emitter on voltage		v CEsat	max. 1.0			V	
$I_C = 2 A$; $V_{CE} = 4 V$		$V_{BE(on)}^*$	max.	1	.4		V
D.C. current gain		V BE(ON)	mux.	1	. 1		V
$I_C = 0.5 A; V_{CE} = 4 V$		h_{FE}^*	min.	40			
IC = 0.3 A, VCE = 0.3 A	ı v	n_{FE}	mu.	7	.0		
$I_C = 2 A; V_{CE} = 4$	V	h_{FE}^*	min.	2	:0		
Transition frequency							
$I_C = 0.5 A; V_{CE} = 4$	4 V; f = 1 MHz	f_T	min.	Ċ	3		MHz
0 1:11 ::							
Switching time $V_{CC} = 20 \text{ V}; I_C = 1$ $I_{con} = 1A; I_{Bon} = -$							
$R_L = 20\Omega$	3.773.7				2		
Turn on time	NPN	t_{on}	typ.		.3		μs
Turn off time	NPN	t_{off}	typ.		.5		μs
	PNP	t_{on}	typ.		.1		μs
	PNP	t_{off}	typ.	0	.4		μs

^{*} Measured under pulse conditions: $t_p \le 300 \mu s$; duty cycle $\le 2\%$

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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